

IN THE CLAIMS:

Please amend the claims as follows:

Q2
1. (Amended) A nitride based semiconductor light emitting device comprising:

a light emitting layer composed of a Group III nitride based semiconductor and including an active layer; and

a cladding layer of a first conduction type composed of a Group III nitride based semiconductor, formed on said light emitting layer, having a larger band gap than said active layer, and having a lower refractive index than the active layer,

the thickness of said cladding layer of a first conduction type being less than 0.3 μm , and

said cladding layer of a first conduction type has an aluminum composition ratio of not more than 0.05.

Q3
14. (Amended) A nitride based semiconductor light emitting device comprising:

a light emitting layer composed of a Group III nitride based semiconductor; and

an electrode which is brought into contact with said light emitting layer, wherein

said light emitting layer includes an active layer and an optical guide layer of a first conduction type formed on said active layer,

said optical guide layer of a first conduction type has a larger band gap than that of said active layer and has a lower refractive index than that of said active layer, and

said electrode is brought into ohmic contact with said optical guide layer.

Please add the following new claims:

25. (New) A nitride based semiconductor laser device comprising:

a light emitting layer composed of a Group III nitride based semiconductor and including an active layer; and

a cladding layer of a first conduction type composed of a Group III nitride based semiconductor, formed on said light emitting layer, having a larger band gap than said active layer, and having a lower refractive index than the active layer,

the thickness of said cladding layer of a first conduction type being less than 0.3 μm .

26. (New) The nitride based semiconductor laser device according to claim 25, wherein said cladding layer of a first conduction type has an aluminum composition ratio of not more than 0.05.

27. (New) The nitride based semiconductor laser device according to claim 25, wherein

said light emitting layer further includes an optical guide layer of a first conduction type formed on said active layer,

said optical guide layer of a first conduction type has a smaller band gap and a higher refractive index than said cladding layer of a first conduction type and has a larger band gap and a lower refractive index than said active layer, and

said cladding layer of a first conduction type is formed on said optical guide layer of a first conduction type.

28. (New) The nitride based semiconductor laser device according to claim 27, wherein
said light emitting layer further includes a carrier leakage preventing layer of a first
conduction type formed on said active layer and having a larger band gap than said optical guide
layer of a first conduction type, and
said optical guide layer of a first conduction type is formed on said carrier leakage preventing
layer of a first conduction type.

29. (New) The nitride based semiconductor laser device according to claim 25, wherein
said cladding layer of a first conduction type has a ridge portion, and
the thickness of said ridged portion is less than 0.3 μm .

30. (New) The nitride based semiconductor laser device according to claim 25, wherein
said Group III nitride based semiconductor contain at least one of boron, gallium, aluminum,
indium, and thallium.

31. (New) The nitride based semiconductor laser device according to claim 25, wherein
said cladding layer of a first conduction type contains gallium and aluminum.

32. (New) The nitride based semiconductor laser device according to claim 25, wherein
said active layer contains gallium and indium.

a4
cont.

33. (New) The nitride based semiconductor laser device according to claim 25, wherein
said active layer has a multi-quantum well structure alternately including one or more well
layers and a plurality of quantum barrier layers, and
the band gap of the active layer is the band gap of said one or more well layers.
34. (New) The nitride based semiconductor laser device according to claim 25, wherein
the electric field distribution of laser light in the active layer is changed in accordance with
a sine function or a cosine function, and
the electric field distribution of laser light in the cladding layer of a first conduction type is
changed in accordance with an exponential function.
35. (New) The nitride based semiconductor laser device according to claim 25, further comprising
a current blocking layer formed on or in said cladding layer of a first conduction type and having a
striped opening.
36. (New) The nitride based semiconductor laser device according to claim 25, wherein
said first conduction type is a p type.
37. (New) The nitride based semiconductor laser device according to claim 25, further comprising
a cladding layer of a second conduction type composed of a Group III nitride based
semiconductor,
said light emitting layer is formed on said cladding layer of a second conduction type.